

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

PABLA

Serial No. 10/088,542

National Phase of: PCT/GB00/03788

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Group: 2812



Filed: March 19, 2002

Examiner: Mulpuri, Savitri

For: SEMICONDUCTOR PROCESS

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April 11, 2003

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

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In response to the Office Action dated December 19, 2002, please amend the above-identified patent application as follows.

IN THE CLAIMS

Please amend claim 1 as follows. A marked-up version of the amended claim showing the revisions thereto is attached.

1. (*Amended*) A method of making a photonic band gap material, the method comprising:

- B'
- (a) growing an epitaxial layer of a first semiconductor material onto a substrate;
 - (b) applying a mask to selected areas of the first semiconductor material and etching away the non-masked areas of the first semiconductor material to form a

plurality of recesses;